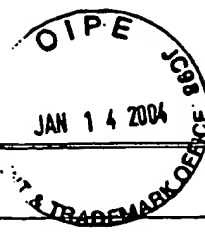


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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
J. G. 91	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
YI	6,204,525 B1	03/20/01	SAKURAI ET AL				
YJ	5,985,404	11/16/99	YANO ET AL				
YK	6,538,359 B1	03/25/03	HIRAKU ET AL				
YL	6,498,358 B1	12/24/02	LACH ET AL				
YM	5,387,811	02/07/95	SAIGOH				
YN	5,523,602	06/04/96	HORIUCHI ET AL				
YO	5,362,998	11/08/94	IWAMURA ET AL				
YQ	5,188,976	02/23/93	KUME ET AL				
Examiner <i>[Signature]</i>					Date Considered <i>2/2/04</i>		
*Examiner Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

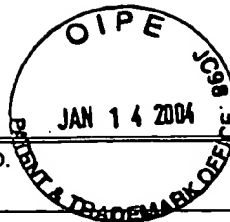
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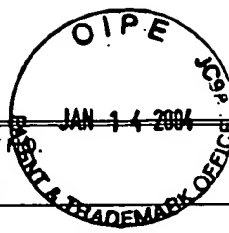
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A. Y.	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
ZQ	5,753,934	05/19/98	YANO ET AL				
ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL				
ZS	6,051,874	04/18/00	MASUDA				
ZT	5,166,761	11/24/92	OLSON ET AL				
ZU	5,574,744	11/12/96	GAW ET AL				
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				FILING DATE July 24, 2001		GROUP 2826	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
q. 1	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT			
1	CCB	2 152 315	07/31/85	GREAT BRITAIN			
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT			
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)			
	CCE	WO 03/012874	02/13/03	WIPO			
	CCF	1 043 427	10/11/00	EUROPE			
	CCG	1 069 605	01/17/01	EUROPE			
	CCH	WO 02/099885	12/12/02	WIPO			
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT			
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)			
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)			
	CCL	WO 02/11254	02/07/02	WIPO			
	CCM	0 494 514	07/15/92	EUROPE			
	CCN	0 247 722	12/02/87	EUROPE			
	CCO	1 037 272	09/20/00	EUROPE			
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)			
CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT				
✓	CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT			
1. 7	CCS	0 392 714	10/17/90	EUROPE			
	CCT						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
9.2	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3	
7	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001	
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3	
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3	
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651	
	LLAF	V. Bormand et al.; "Deposition of LiTaO <sub>3</sub> thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244	
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296	
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr <sub>0.52</sub> Ti <sub>0.48</sub> )O <sub>3</sub> epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460	
	LLAI	Dwight C. Streit et al.; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US	
	LLAJ	C. Y. Hung et al.; "Piezoelectrically Induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US	
	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287	
	LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958	
	LLAM	M.R. Wilson et al.; "GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246	
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO <sub>3</sub> at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169	
11.4	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536	
	LLAP		
	LLAQ		
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